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buckled germanium selenide

Author: H. Arkın E. Aktürk

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*Highlights (for review)

- Buckled GeSe (b-GeSe) has a stable honeycomb structure
 b-GeSe is a semiconductor with a indirect band gap of 2.29 eV.
 In low coverage, b-GeSe attains half metallicity through the adsorption of Si, Ge, P and Br.

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